

9. (Amended) A flash memory comprising:

B1
a semiconductor substrate that includes a flash memory cell that has a floating gate;

a conductive layer formed on the substrate; and

a passivation layer formed on the conductive layer that is not transparent to ultraviolet light, the passivation layer covering the flash memory cell. *new matter*

B2
12. (Amended) The flash memory of claim 11 wherein the flash memory cell's floating gate has a gate length that is less than about 0.5 microns.